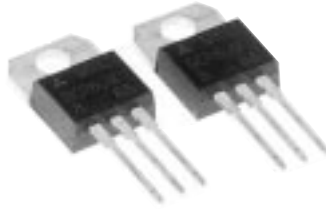


BCR8UM

MEDIUM POWER USE
INSULATED TYPE, GLASS PASSIVATION TYPE

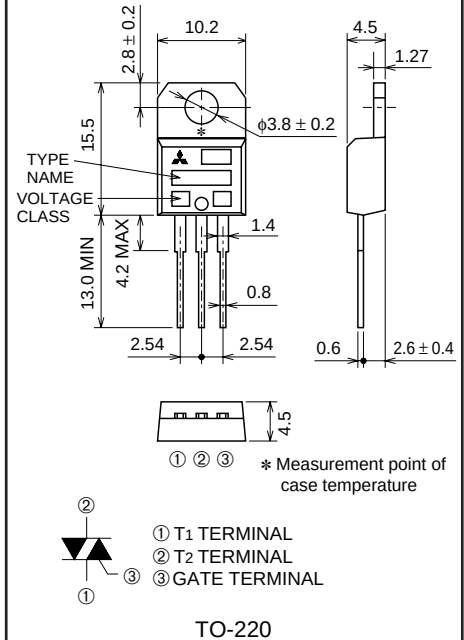
BCR8UM



- I_T (RMS) 8A
- V_{DRM} 400V/600V
- I_{FGT} I, I_{RGT} I, I_{RGT} III 15mA
- V_{iso} 1500V

OUTLINE DRAWING

Dimensions
in mm



APPLICATION

Light dimmer

MAXIMUM RATINGS

Symbol	Parameter	Voltage class		Unit
		8	12	
V_{DRM}	Repetitive peak off-state voltage *1	400	600	V
V_{DSM}	Non-repetitive peak off-state voltage *1	500	720	V

Symbol	Parameter	Conditions	Ratings	Unit
I_T (RMS)	RMS on-state current	Commercial frequency, sine full wave 360° conduction, $T_c=94^\circ\text{C}$ *3	8	A
I_{TSM}	Surge on-state current	60Hz sinewave 1 full cycle, peak value, non-repetitive	80	A
I^2_t	I^2_t for fusing	Value corresponding to 1 cycle of half wave 60Hz, surge on-state current	26	A ² s
PGM	Peak gate power dissipation		5	W
PG (AV)	Average gate power dissipation		0.5	W
VGM	Peak gate voltage		10	V
IGM	Peak gate current		2	A
T_j	Junction temperature		-40 ~ +125	°C
T_{stg}	Storage temperature		-40 ~ +125	°C
—	Weight	Typical value	2.3	g
V_{iso}	Isolation voltage	$T_a=25^\circ\text{C}$, AC 1 minute, T1 · T2 · G terminal to case	1500	V

*1. Gate open.

BCR8UM

MEDIUM POWER USE
INSULATED TYPE, GLASS PASSIVATION TYPE

ELECTRICAL CHARACTERISTICS

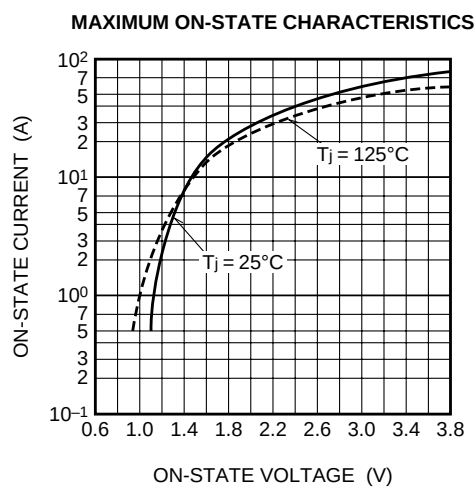
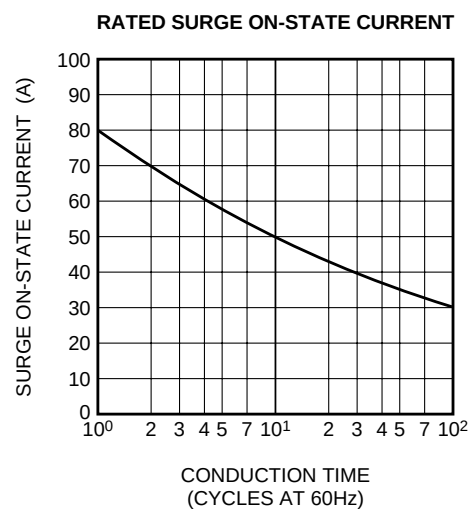
Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
IDRM	Repetitive peak off-state current	T _J =125°C, V _{DRM} applied	—	—	2.0	mA
V _{TM}	On-state voltage	T _C =25°C, I _{TM} =12A, Instantaneous measurement	—	—	1.5	V
V _{FGT} I	Gate trigger voltage *2	T _J =25°C, V _D =6V, R _L =6Ω, R _G =330Ω	—	—	1.5	V
V _{RGT} I			—	—	1.5	V
V _{RGT} III			—	—	1.5	V
I _{FGT} I	Gate trigger current *2	T _J =25°C, V _D =6V, R _L =6Ω, R _G =330Ω	—	—	15	mA
I _{RGT} I			—	—	15	mA
I _{RGT} III			—	—	15	mA
V _{GD}	Gate non-trigger voltage	T _J =125°C, V _D =1/2V _{DRM}	0.2	—	—	V
R _{th} (j-c)	Thermal resistance	Junction to case *3 *4	—	—	3.0	°C/W

*2. Measurement using the gate trigger characteristics measurement circuit.

*3. Case temperature is measured at the T₂ terminal 1.5mm away from the molded case.

*4. The contact thermal resistance R_{th} (c-f) in case of greasing is 1.0°C/W.

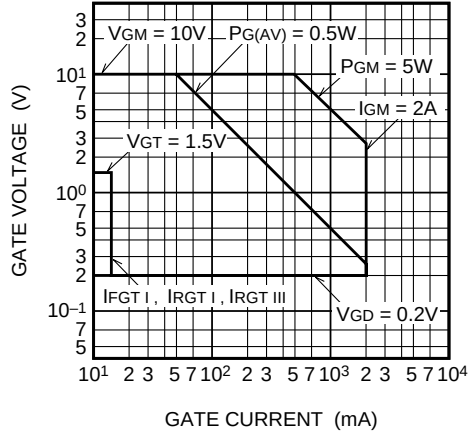
PERFORMANCE CURVES



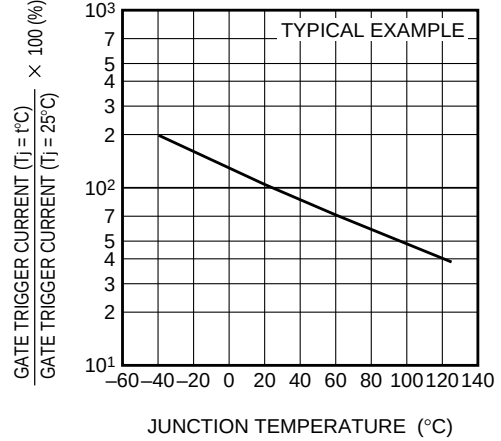
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MEDIUM POWER USE
INSULATED TYPE, GLASS PASSIVATION TYPE

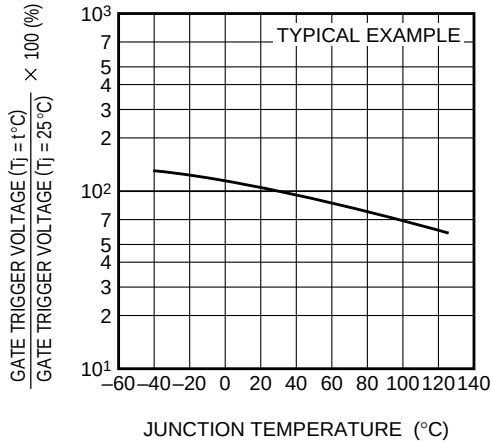
GATE CHARACTERISTICS



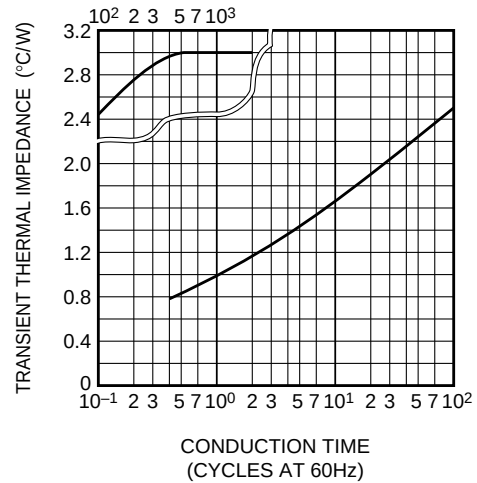
GATE TRIGGER CURRENT VS. JUNCTION TEMPERATURE



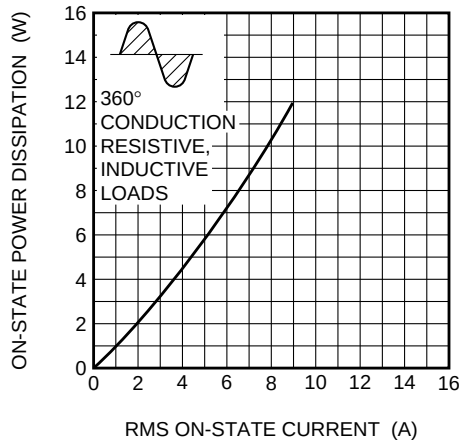
GATE TRIGGER VOLTAGE VS. JUNCTION TEMPERATURE



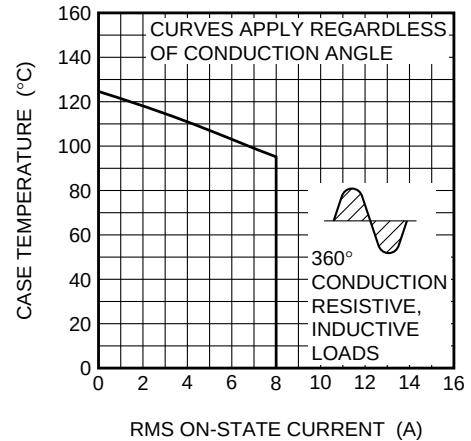
MAXIMUM TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS (JUNCTION TO CASE)



MAXIMUM ON-STATE POWER DISSIPATION

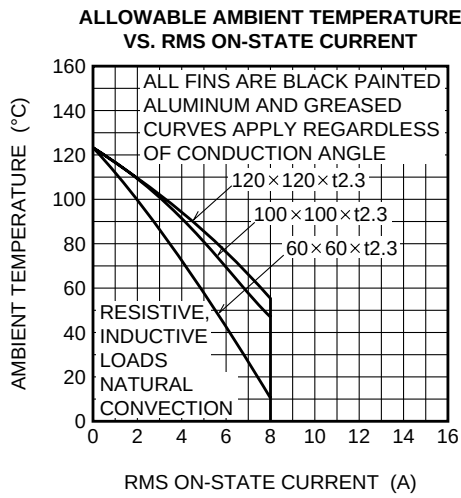
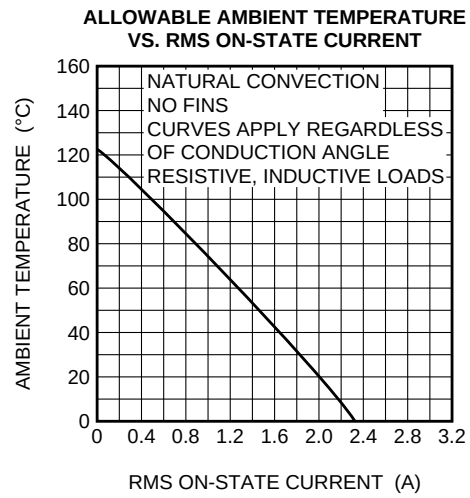
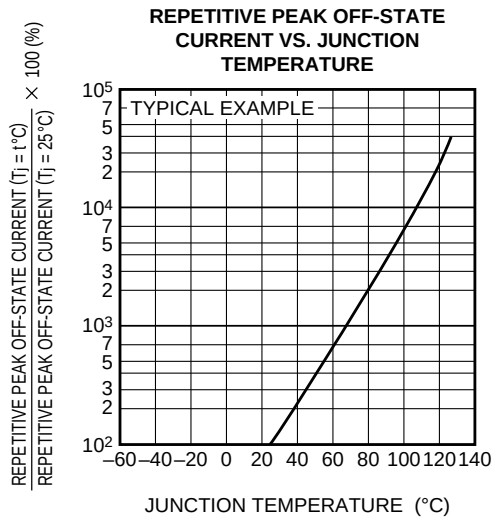
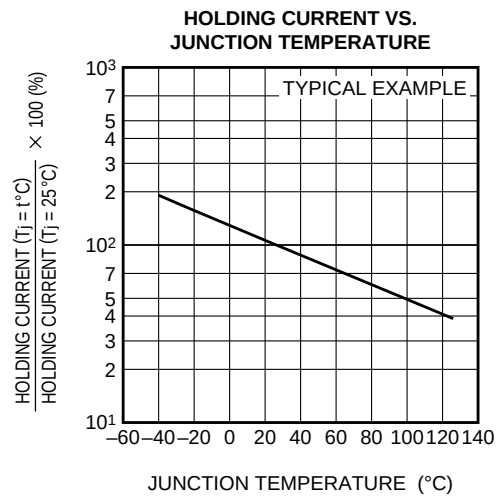
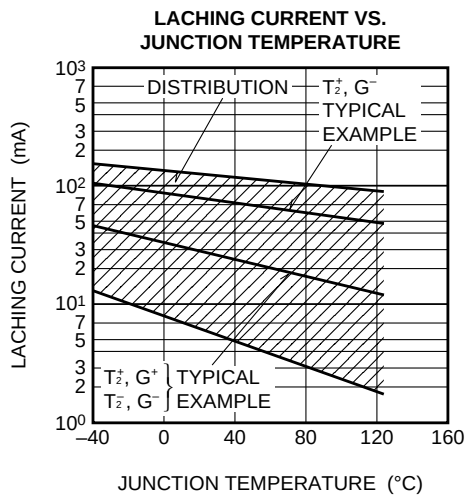
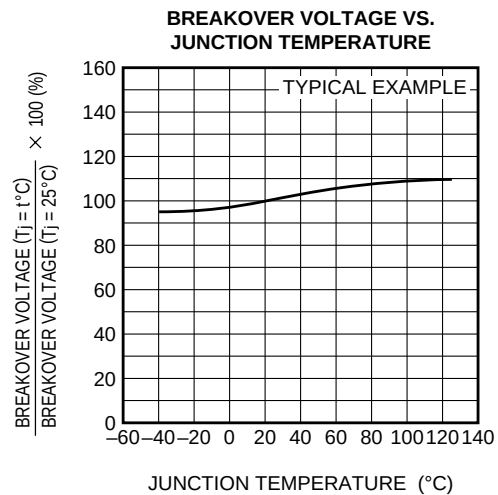


ALLOWABLE CASE TEMPERATURE VS. RMS ON-STATE CURRENT



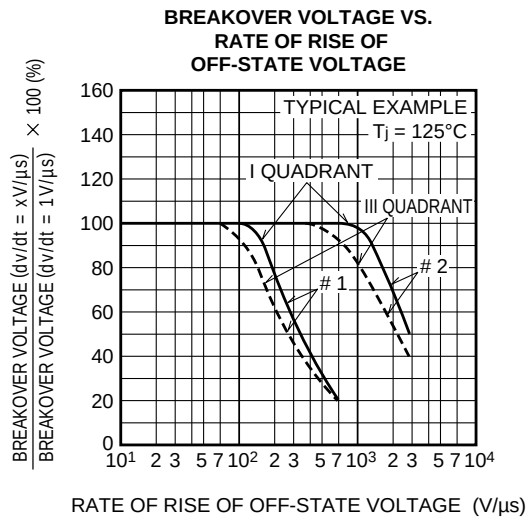
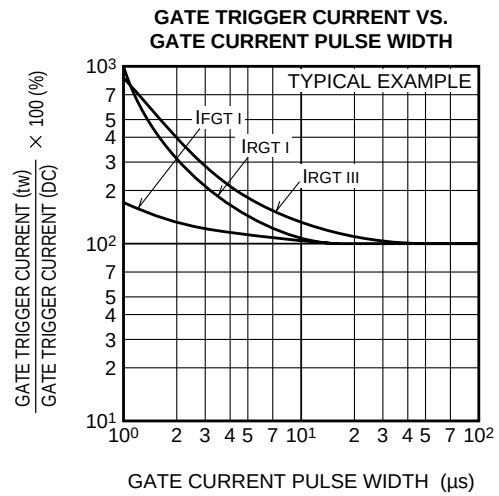
BCR8UM

MEDIUM POWER USE
INSULATED TYPE, GLASS PASSIVATION TYPE



BCR8UM

MEDIUM POWER USE
INSULATED TYPE, GLASS PASSIVATION TYPE



GATE TRIGGER CHARACTERISTICS TEST CIRCUITS

